

Linear™ Power MOSFET IXTH2N150L

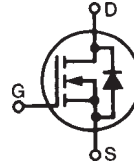
w/Extended FBSOA

$$V_{DSS} = 1500V$$

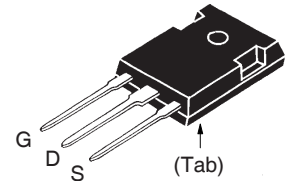
$$I_{D25} = 2A$$

$$R_{DS(on)} \leq 15\Omega$$

N-Channel Enhancement Mode
Guaranteed FBSOA
Avalanche Rated



TO-247



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$	1500	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	2	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	6	A
P_D	$T_C = 25^\circ\text{C}$	290	W
T_J		-55 to +150	$^\circ\text{C}$
T_{JM}		+150	$^\circ\text{C}$
T_{stg}		-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	Plastic Body for 10s	260	$^\circ\text{C}$
M_d	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in
Weight		6	g

Features

- Designed for Linear Operation
- International Standard Package
- Avalanche Rated
- Guaranteed FBSOA at 75°C

Advantages

- Easy to Mount
- Space Savings
- High Power Density

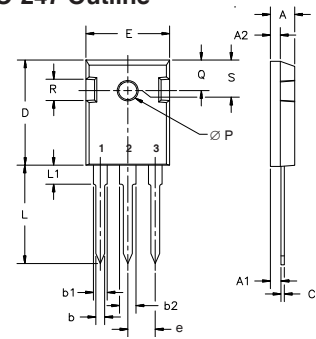
Applications

- DC Choppers
- DC-DC Converters
- Battery Chargers
- Programmable Loads
- Current Regulators
- Temperature and Lighting Controls

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu\text{A}$	1500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	6.0		8.5 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$			15 μA
	$T_J = 125^\circ\text{C}$			150 μA
$R_{DS(on)}$	$V_{GS} = 20V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			15 Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}, I_D = 0.5 \cdot I_{D25}$, Note 1	0.4	0.7	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		1470	pF
C_{oss}			92	pF
C_{rss}			30	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 15\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 10\Omega$ (External)		33	ns
t_r			55	ns
$t_{d(off)}$			85	ns
t_f			84	ns
$Q_{g(on)}$	$V_{GS} = 20\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		72	nC
Q_{gs}			15	nC
Q_{gd}			30	nC
R_{thJC}			0.43	$^\circ\text{C/W}$
R_{thCS}		0.21		$^\circ\text{C/W}$

TO-247 Outline



Terminals: 1 - Gate 2 - Drain
3 - Source

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

Safe Operating Area Specification

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 1200\text{V}, I_D = 0.10\text{A}, T_C = 75^\circ\text{C}, T_P = 5\text{s}$	120		W

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			2 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			8 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 2\text{A}, -di/dt = 100\text{A}/\mu\text{s},$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$		1.86	μs
I_{RM}			24	A
Q_{RM}			22	μC

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

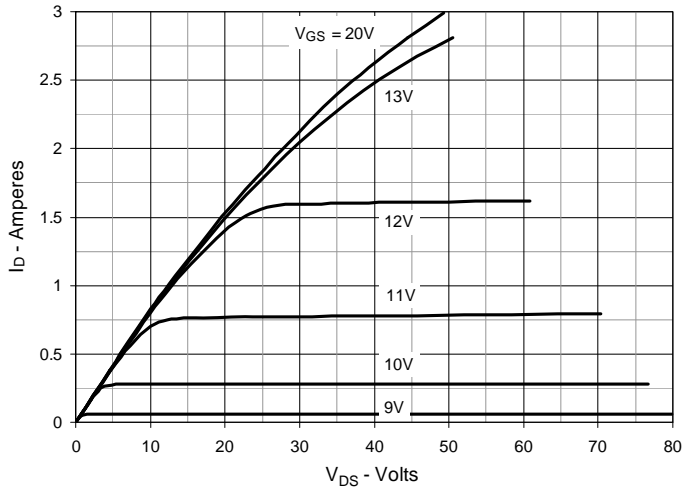


Fig. 2. Output Characteristics @ $T_J = 125^\circ\text{C}$

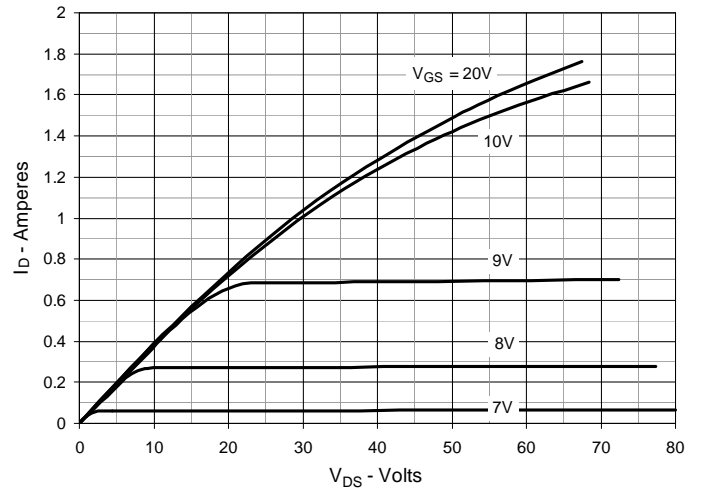


Fig. 3. $R_{DS(on)}$ Normalized to $I_D = 1\text{A}$ Value vs. Junction Temperature

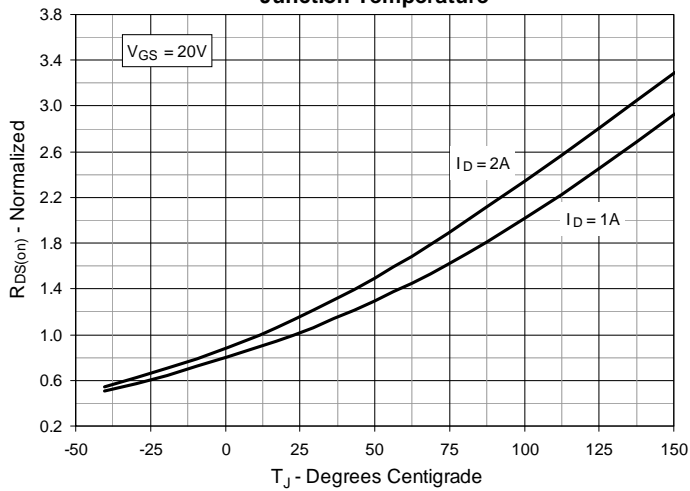


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 1\text{A}$ Value vs. Drain Current

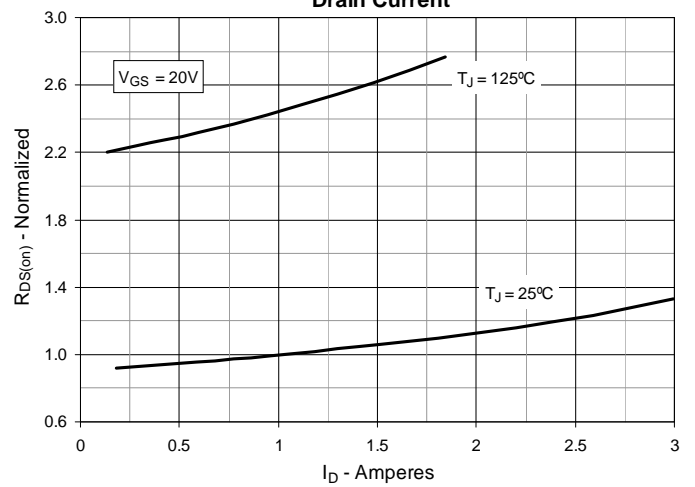


Fig. 5. Maximum Drain Current vs. Case Temperature

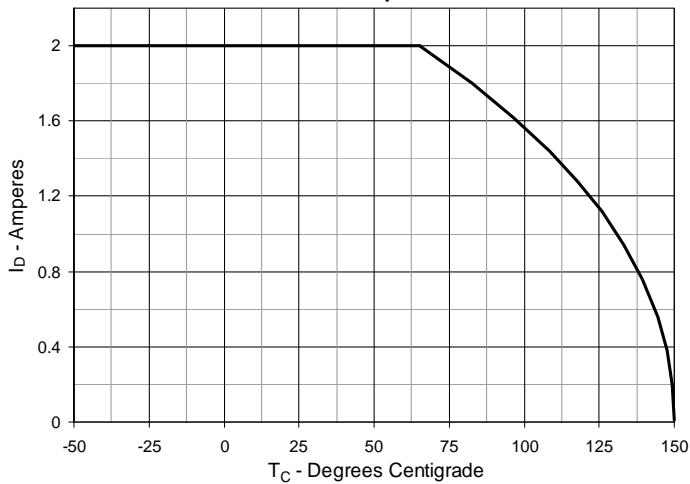


Fig. 6. Input Admittance

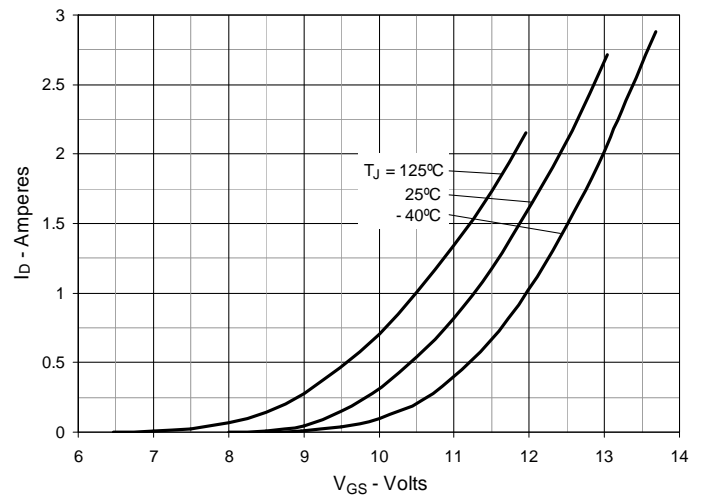


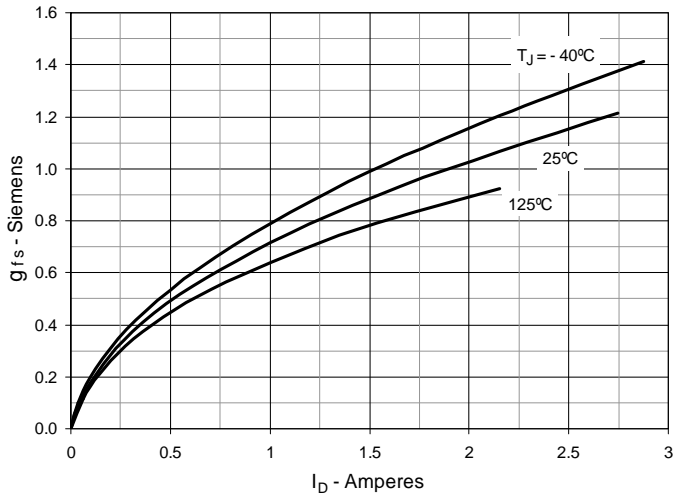
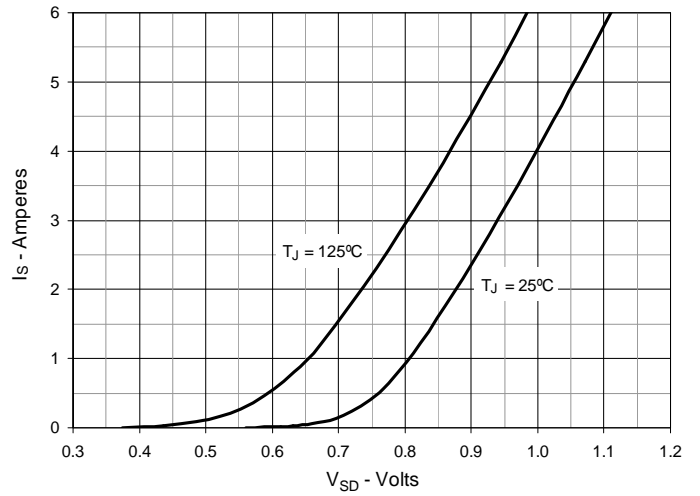
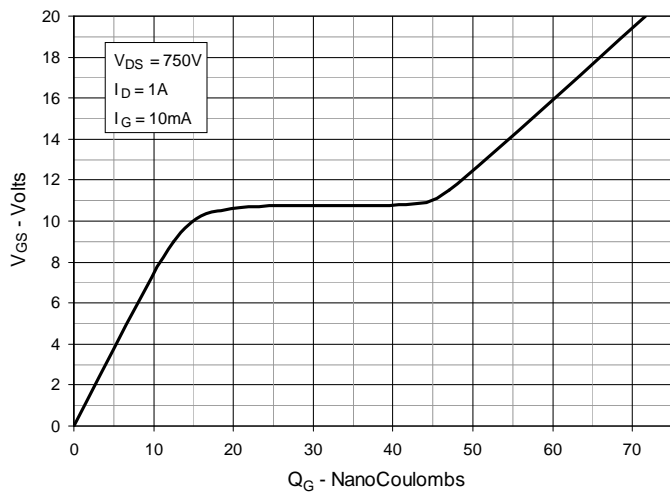
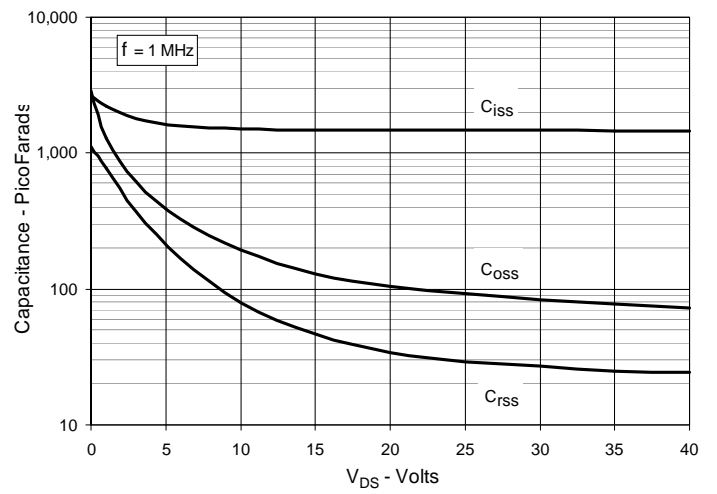
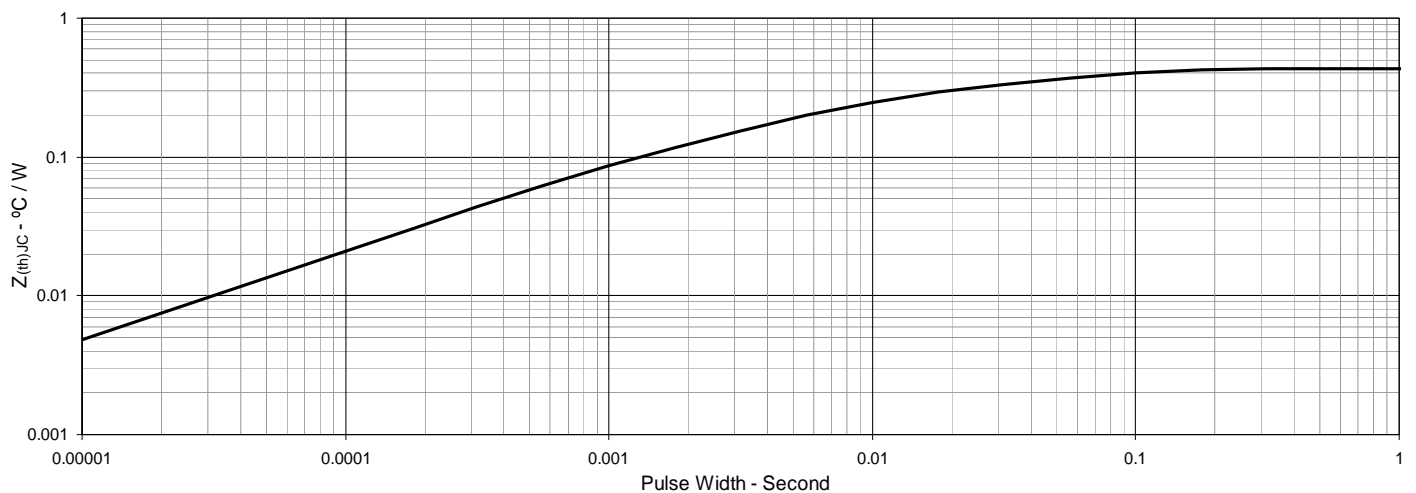
Fig. 7. Transconductance

Fig. 8. Forward Voltage Drop of Intrinsic Diode

Fig. 9. Gate Charge

Fig. 10. Capacitance

Fig. 11. Maximum Transient Thermal Impedance


Fig. 12. Forward-Bias Safe Operating Area
@ $T_C = 25^\circ\text{C}$

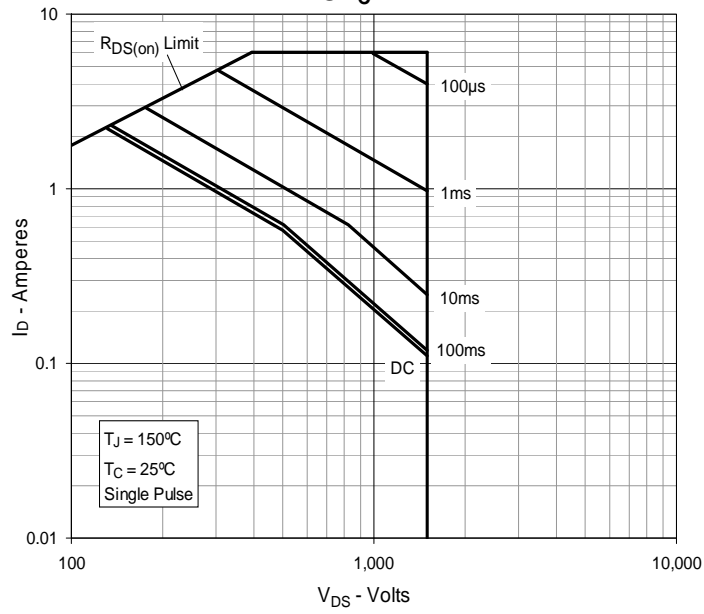


Fig. 13. Forward-Bias Safe Operating Area
@ $T_C = 75^\circ\text{C}$

